

Title (en)  
PLASMA ETCHING SYSTEM

Title (de)  
PLASMAÄTZANLAGE

Title (fr)  
INSTALLATION DE GRAVURE AU PLASMA

Publication  
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Application  
**EP 01944922 A 20010510**

Priority  
• DE 0101777 W 20010510  
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Abstract (en)  
[origin: WO0188950A1] The invention relates to a plasma etching system (5) particularly for anisotropically etching a substrate (13) by the action of a plasma (21). Said system comprises a first, especially inductively coupled plasma production device (31) which is provided with a first means (11) for generating a first high frequency electromagnetic alternating field; an etching chamber for producing a first plasma (21) from charged particles as a result of the action of said first high frequency electromagnetic alternating field on a first reactive gas with the substrate to be etched; and a first gas supply. A second upstream plasma production device (32) is connected to said first plasma production device (31). Said second plasma production device comprises a second means (20), especially a microwave generator (20), for generating a second high frequency electromagnetic alternating field; a plasma production area (33) for producing a second plasma (18) from charged particles as a result of the action of said second high frequency electromagnetic alternating field on a second reactive gas; and a second gas supply (16). The second plasma (18) thus produced can be fed to the first plasma production device (31) at least partially in the form of a reactive gas via the first gas supply (32).

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